ICP Etcher Series

Uni-body Design Concept

Foot-print outstanding (ref 1.0m*1.5m)

Process Design Kits

Better process performance

Chamber Control

Chamber liner, electrode temperature control suitable for different process application

Configurable Plasma Discharge Gap

Tuned as a parameter dependently

Cost or Performance Orientation

RF, Pump, Values etc. depending on requirements

Plasma Specialization

Low power plasma technology, ion damage-free optional

Sample Handling Options

Open-Load or Load-Lock

Specification	Parameters
Wafer Size Range	4,6,8,12 inch or multi-wafers optional
Etching Materials	Si-Based (Si/SiO2/SiNx/SiC/Quartz etc.), Compounds (InP/GaN/GaAs/Ga2O3 etc.), 2D Materials (MoS2/BN/Graphene etc.), Metals (W/Ta/Mo etc.), Diamond, Failure Analysis, etc.
Vacuum	TMP&Mechanical Pump
RF Power	Source 1000-3000W, Bias 300-1000W, optional
Gas System	5 lines(Standard) and He backside cooling, or customized
Wafer Stage Temperature Range	From -70℃ to 200℃, optional
Non-Uniformity	Less than ±5% (Edge Exclusion)